SKET 330



SEMIPACK® 4

Thyristor Modules

SKET 330

Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

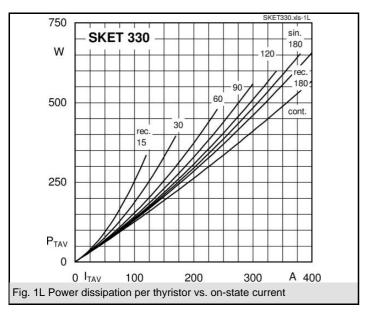
Typical Applications

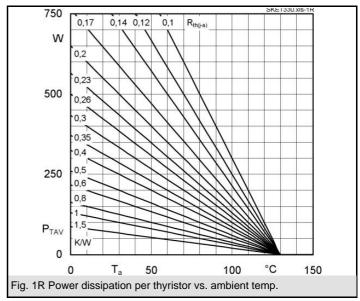
- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)
- 1) See the assembly instructions
- 2) The screws must be lubricated

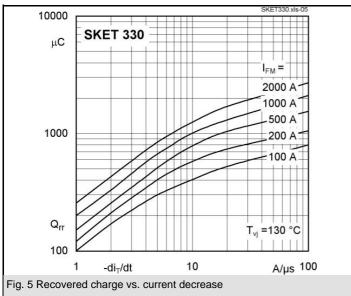
V_{RSM}	V_{RRM}, V_{DRM}	I _{TRMS} = 600 A (maximum value for continuous operation)	
V	V	$I_{TAV} = 330 \text{ A (sin. } 180; T_c = 78 ^{\circ}\text{C})$	
900	800	SKET 330/08E	
1300	1200	SKET 330/12E	
1500	1400	SKET 330/14E	
1700	1600	SKET 330/16E	
1900	1800	SKET 330/18E	
2100	2000	SKET 330/20E	
2300	2200	SKET 330/22E	

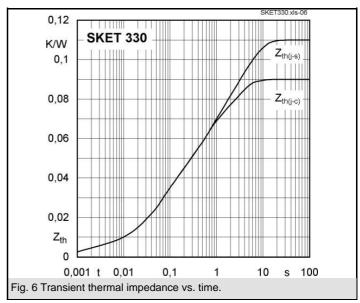
Symbol	Conditions	Values	Units
I _{TAV}	sin. 180; T _c = 85 (100) °C	295 (210)	Α
I _D	P16/300F; T _a = 35 °C; B2 / B6	530 / 665	Α
I _{RMS}	P16/400F; T _a = 35 °C; W1 / W3	685 / 3 * 550	Α
I _{TSM}	T _{vi} = 25 °C; 10 ms	9000	Α
	T _{vi} = 130 °C; 10 ms	8000	Α
i²t	T _{vj} = 25 °C; 8,3 10 ms	405000	A²s
	T _{vj} = 130 °C; 8,3 10 ms	320000	A²s
V_{T}	T _{vi} = 25 °C; I _T = 1500 A	max. 2,05	V
$V_{T(TO)}$	T _{vi} = 130 °C	max. 1,2	V
r _T	T _{vj} = 130 °C	max. 0,55	mΩ
$I_{DD}; I_{RD}$	T_{vj} = 130 °C, V_{RD} = V_{RRM} , V_{DD} = V_{DRM}	max. 120	mA
t _{gd}	$T_{vj} = 25 \text{ °C}; I_G = 1 \text{ A}; di_G/dt = 1 \text{ A/}\mu\text{s}$	1	μs
t _{gr}	$V_{\rm D} = 0.67 * V_{\rm DRM}$	2	μs
(di/dt) _{cr}	T _{vi} = 130 °C	max. 125	A/µs
(dv/dt) _{cr}	T _{vi} = 130 °C	max. 1000	V/µs
t_q	$T_{vj}^{3} = 130 ^{\circ}\text{C}$	150 200	μs
I _H	T_{vj} = 25 °C; typ. / max.	150 / 500	mA
IL	T_{vj} = 25 °C; R_G = 33 Ω ; typ. / max.	500 / 2000	mA
V _{GT}	T _{vj} = 25 °C; d.c.	min. 3	V
I _{GT}	$T_{vj}^{'} = 25 ^{\circ}\text{C}; \text{d.c.}$	min. 200	mA
V_{GD}	$T_{vj} = 130 ^{\circ}\text{C}$; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 130 °C; d.c.	max. 10	mA
R _{th(j-c)}	cont.	0,09	K/W
R _{th(j-c)}	sin. 180	0,095	K/W
$R_{th(j-c)}$	rec. 120	0,11	K/W
R _{th(c-s)}		0,02	K/W
T_{vj}		- 40 + 130	°C
T_{stg}		- 40 + 130	°C
V _{isol}	a. c. 50 Hz; r.m.s.; 1s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminal	17 ± 15 % ²⁾	Nm
а		5 * 9,81	m/s²
m	approx.	940	g
Case		A 36	

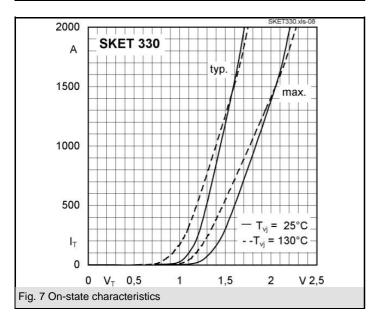


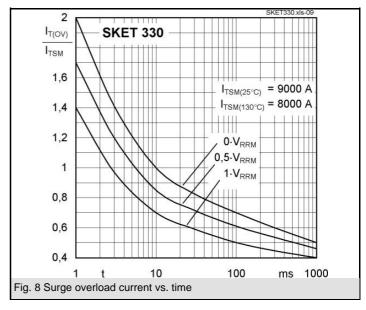


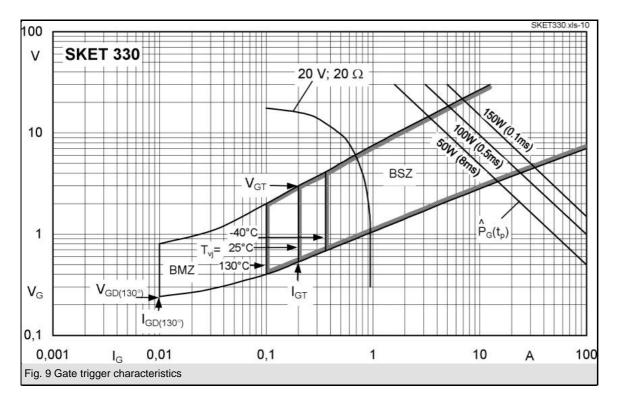


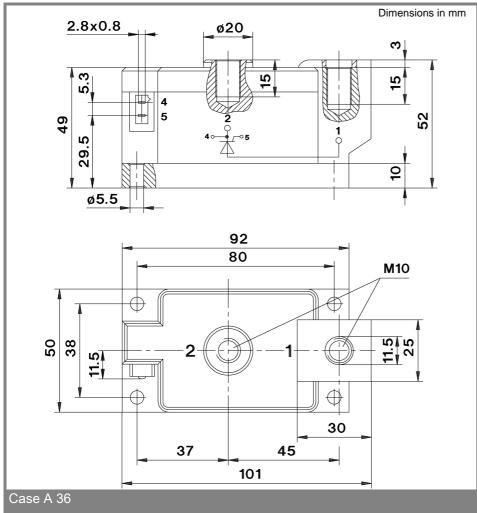












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